

**IN THE SPECIFICATION**

Please substitute the corresponding paragraph with the following amended paragraph.

In the paragraph starting on page 15, line 4:

In one version, a two-step mask material etch may be performed. For example, a first step may comprise exposing mask material **240** to process gas comprising a composition that is substantially absent a polymer forming gas and the second step may comprise exposing the mask material **240** to process gas having a composition comprising a polymer forming gas. In one particular version, the first mask material etchant gas may comprise a fluorine-containing gas, for example, in one version, the first mask material etchant gas comprises one or more of  $\text{CF}_4$ ,  $\text{C}_2\text{F}_6$ ,  $\text{NF}_3$ , and  $\text{SF}_6$ , and the second mask material etchant gas may comprise one or more of  $\text{CHF}_3$ ,  $\text{CH}_2\text{F}_2$ , and  $\text{CH}_3\text{F}$ , with or without one or more of  $\text{CF}_4$ ,  $\text{C}_2\text{F}_6$ ,  $\text{NF}_3$ , and  $\text{SF}_6$ . The first or second mask material etchant gases may also comprise an inert or carrier gas, such as Ar, He, or N to aid in controlling sputtering and/or dilution. In this version, the etchant residue formed during processing of a previous substrate may be cleaned from the chamber surfaces **275** before polymeric residues are formed and deposited thereon. This can result in easier removal of the etchant deposits. Sandwich deposits comprising a layer of silicon-containing etchant residue and a layer of polymer can be difficult to clean and can result in flaking during substrate processing that can affect the quality of the processing. By first introducing a non-polymerizing mask etching gas, the mask material **240** may be etched and the etchant residue may be cleaned from the chamber surfaces **275** before the polymeric residue is formed and deposited on the chamber surfaces **275**. It is advantageous to use the mask material etchant gas comprising polymer forming gas because it aids in etch process performance.